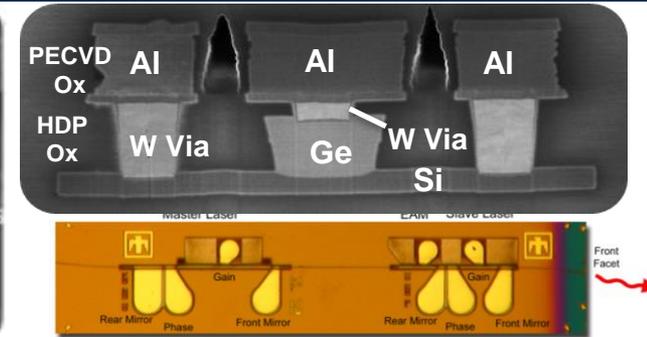
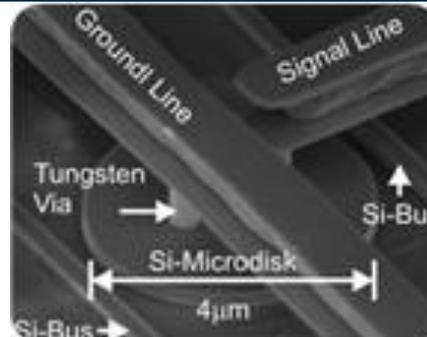


*Exceptional service in the national interest*



## Sandia National Laboratories and the Integrated Photonics Innovative Manufacturing Institute (IP-IMI)

**F. B. (Rick) McCormick, Ph.D.**

Sr. Manager: Microsystems Process Science & Technology Group

Microsystems Science, Technology & Components Center

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<http://www.sandia.gov/mstc/IPIMI>

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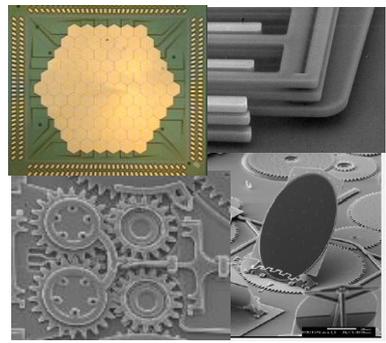
# Why Sandia and the IP-IMI?

- **Expertise:** >20 years in III-V & Silicon Photonics R&D:
  - Toolboxes for internal and contract R&D
- **Capability:** Large flexible Si & III-V R&D Fab, Production rigor:
  - 65kft<sup>2</sup> fab, 10 epi reactors, >60 photonics staff, (60% Ph.D.)
  - Here today, here tomorrow...(NW IC deliveries)
  - Secure environment & staff, robust info-control (TRUST)
- **History of Technology Transfer to Industry:**



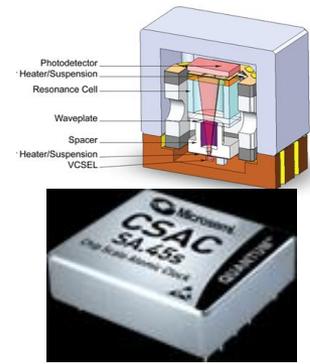
## MEMS (Fairchild)

Transfer of Sandia's Summit IV™ MEMS technology. Network Photonics Optical MEMS



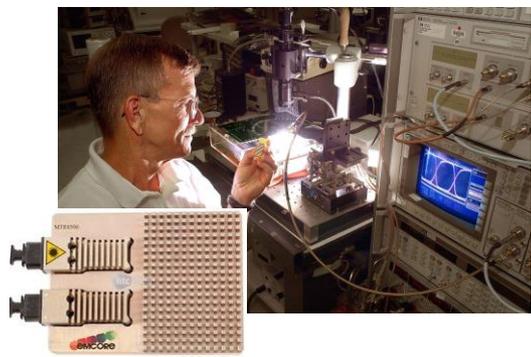
## VCSEL CSAC (Microsemi)

Narrow  $\lambda$  temp-stable VCSEL for Chip-scale Atomic Clock (DARPA)



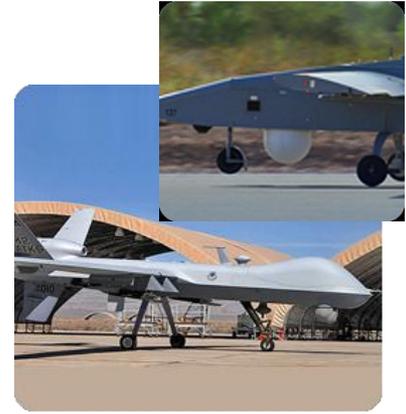
## POM (EMCORE)

OC-192 Transponder Parallel Fiber Optic Module prototype development using VCSEL & PD arrays



## SAR (General Atomics)

Copperhead & Lynx SAR (w/ GA Aero) on TigerShark & Predator UAVs ( [IED detector being transferred to Army](#) )



# What is Sandia National Lab?

## 1950s

NW production engineering & manufacturing engineering

## 1960s

Development engineering  
Vietnam conflict

## 1970s

Multiprogram laboratory  
Energy crisis

## 1980s

Missile defense work  
Cold War

## 1990s

Post-Cold War transition  
Stockpile stewardship

## 2000s

Expanded national security role post 9/11

## 2010s

LEPs  
New START  
Evolving national security challenges



- DOE FFRDC: Initially Z-division of Manhattan Project (Non-nuclear Components, Weaponization of NEP)
- **National security tech transition:** Gov't Agencies (&/or Academia) → SNL → Industry
- DOE supports our "Strategic Partnership Projects" (with Industry & other gov't agencies (OGAs))
- Our Big 3: **Non-compete with Industry, Fairness of Opportunity, No Organizational Conflict of Interest**
- Managed by LMC, but see OCI above
- **CRADAs with many Defense Contractors, Many STTRs & SBIRs, BAA response teaming**
- **Experience handling sensitive & proprietary information**

# Microsystems and Engineering Sciences Applications (MESA): 400,000 Sq-ft Complex with >650 Employees in Secure Facility

- Trusted Digital, Analog, Mixed Signal & RF Integrated Circuits Design & Fabrication
- Custom IC Design
  - Secure microcontrollers
  - Sensor Readout ICs
  - Analog/Digital/RF
  - IBM Trusted Foundry
  - Tamper Resistant
- Micromachining
- RAD Effects and Assurance
- Failure Analysis, Reliability Physics
- Test & Validation
- 3-D Integration Features

## Silicon Fabrication

Si

## Compound Semiconductor Fabrication

III-V

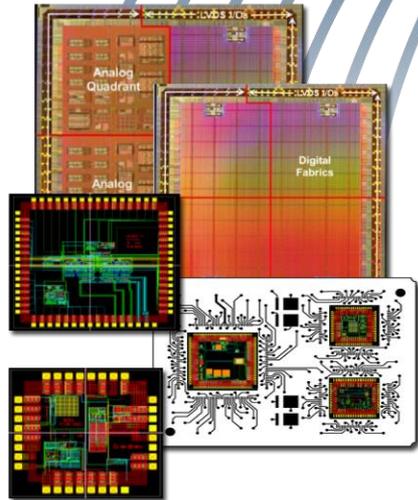
- Advanced Computation
- Modeling & Simulation
- COTS Qualification
- Advanced Packaging
- Custom Electronic Components
- System Design & Test

## Materials Research

- Compound Semiconductor Epitaxial Growth (UV-THz)
- Photonics: Si & III-V
- MEMS, VCSELs, Plasmonics
- Specialized Sensors, FPAs
- Materials Science, Graphene
- Nanotechnology, Chem/Bio
- Heterogeneous-Technology Integration & Processing
- III-V Semiconductor Devices
  - Rad-Hard  $\mu$ Electronics
  - Rad-hard Optical Links
  - Solid-State RF Devices
  - GaN Power Electronics

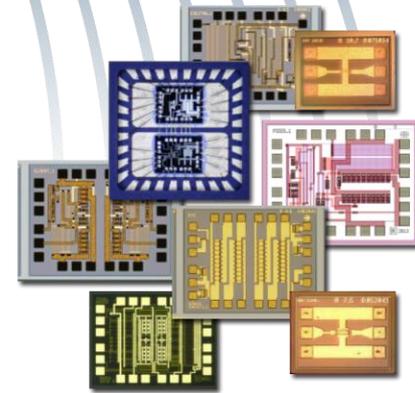
***MESA is an FFRDC-based development and production facility for any microsystem component or technology that cannot or should not be obtained commercially.***

# MESA manufactures strategic radiation-hardened trusted components for Nuclear Weapons



**Radiation Hardened ASICs**

- >25,000 deliveries



**Rad-Hard III-V  $\mu$ Electronics**

- >150,000 deliveries

***TRUST environment (NW, DMEA)***

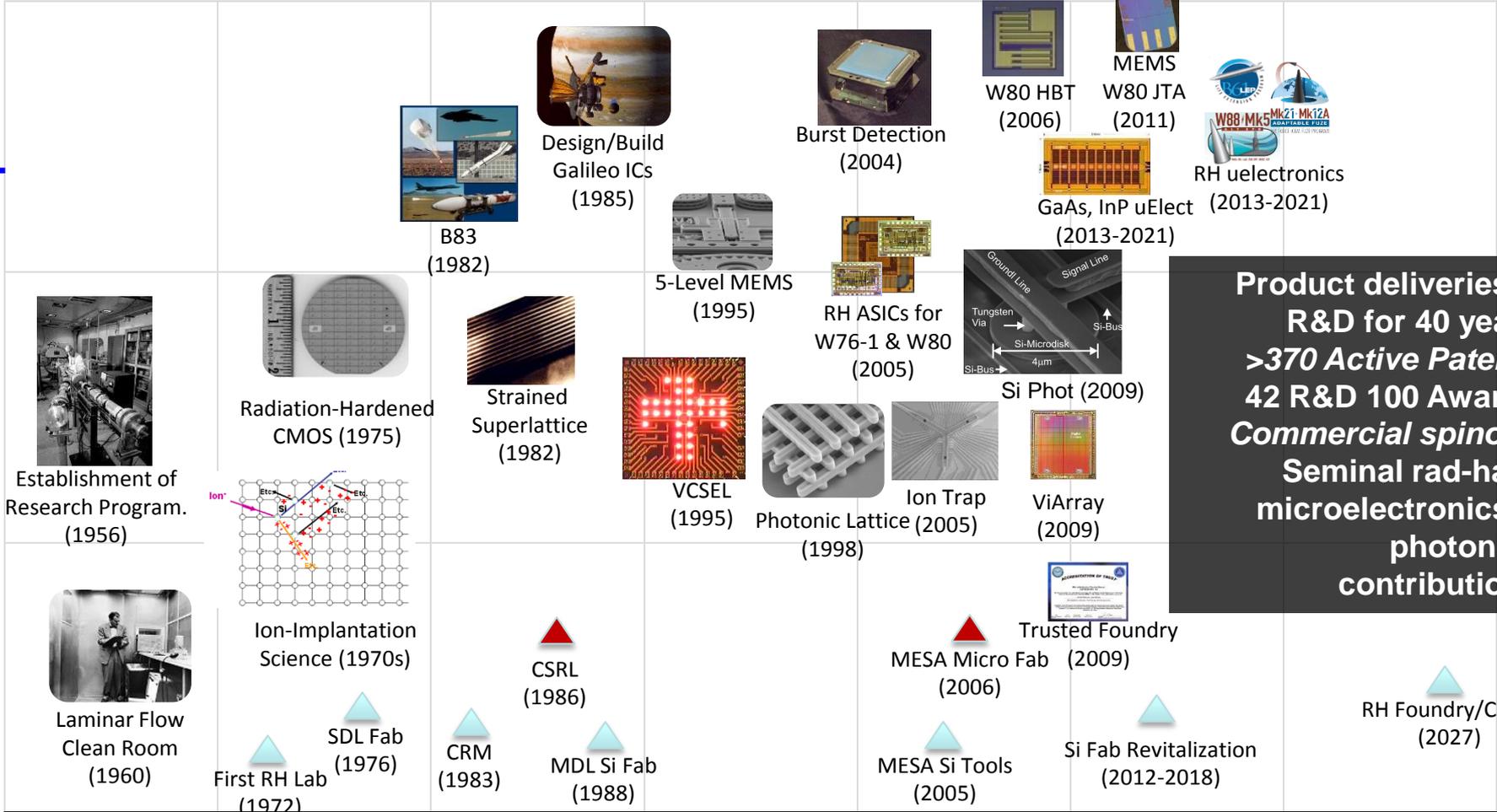
***Strong Failure Analysis/Reliability***

# R&D enables and sustains Sandia's Radiation-Hardened Microelectronics/Microsystems Capability

Impact

Research

Facilities



**Product deliveries & R&D for 40 years**  
**>370 Active Patents**  
**42 R&D 100 Awards**  
**Commercial spinoffs**  
**Seminal rad-hard microelectronics & photonics contributions**

1958      1970      1980      1990      2000      2010      2020      2030

**MISSION: Invent and mature integrated circuit and microsystems technologies that provide differentiation and impact for NW and other national security missions**

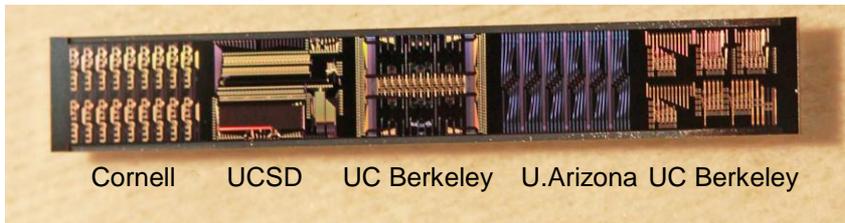
- **SUMMIT V: 5 layer polysilicon MEMS process**

- Developed design manual, DRC, many MPWs over the last decade

- **CMOS7 Electronics: Rad-hard, mixed-signal ASIC/ViaArray: 0.35um, 3.3V core, 3.3V I/O, Cadence, MPWs since 2009**

- **SPP1 Silicon Photonics Process:**

- 250nm Si/3000nm BOx
  - fJ/bit mods, 45 GHz dets, filters, etc.
  - SiN 2-layer guides/xovers
  - Design manual, initial DRC, pilot MPW runs



#### 4. TECHNOLOGY OVERVIEW



Sandia National Laboratories (SNL) has developed a Microsystems and Engineering Sciences Center (MES) located in a limited classified area. Trusted custom fabrication of silicon and silicon nitride technologies for digital, analog and mixed signal ICs is currently available. The MES provides micro-electronics components to support special DOE and NSA Complex is designed to integrate the numerous scientific disciplines including electrical, mechanical, chemical, and materials. The center of SNL's research, development, and prototyping activities. This suite of facilities includes 400,000 square feet and includes cleanroom facilities, laboratories and

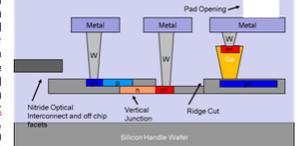
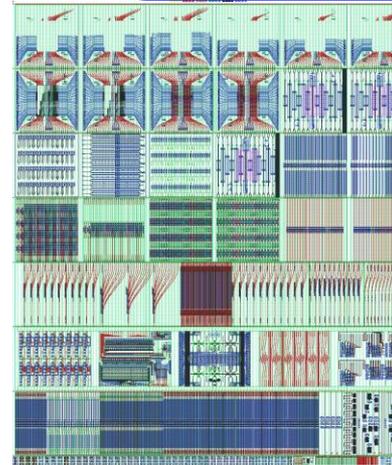
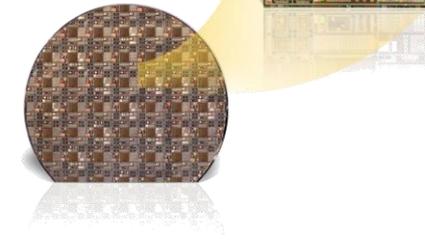
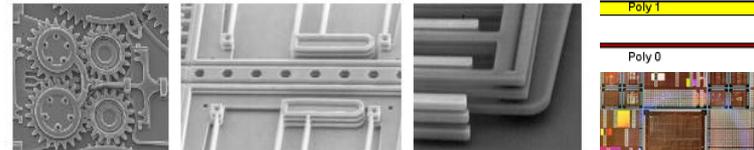
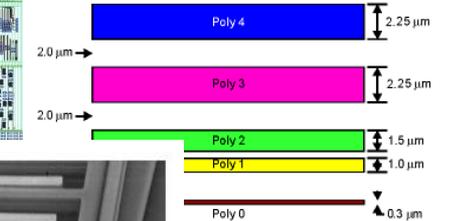


Figure 4-1 A cartoon illustration of the cross-section of Sandia's SPP1 process with a subset of the possible implant configurations

The silicon photonic process (SPP1) has been engineered and matured in the MESA which can be seen in the silicon photonic process is an integrated circuit insulator (SOI) wafer thin SPP1 are two layers one in crystalline silicon and silicon nitride, a full to provide active p-n junctions and resistance ohmic interconnect layer(s), thin of Germanium with all surrounded by silicon nitride. The silicon photonic process technology of photonic integrated circuits (PICs) SPP1 has enabled various device demonstrations, including ultra low energy optical modulators [4], high speed photodetectors [5], high speed optical modulators [6] and the resonant frequency optical filters [7] and modulators [8].

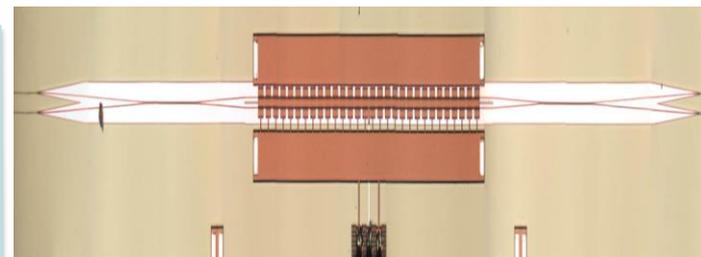
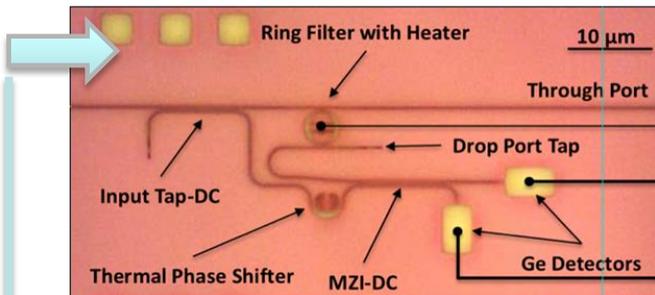
#### PROCESS DETAILS

The process flow of are described in Table 5-1. The base process can be broken

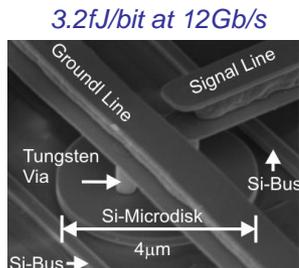


# Trusted Advanced Pathfinder Products: Si Photonics

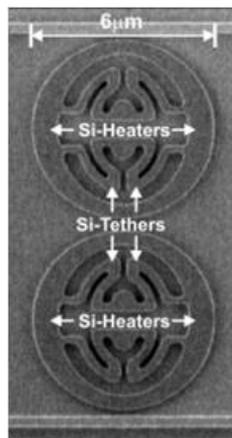
- 2014 *balanced homodyne resonant wavelength stabilization > 55C*
- 2013 *Si Photonics MPW (CIAN NSF ERC)*
- 2012 *24 GHz Si TW MZM*
- 2011 *45 GHz Ge Detector*
- 2010 *3 fJ/bit resonator modulator, 1V-cm MZM*
- 2009 *wavelength tunable rings over 35 nm*
- 2008 *2.4 ns Wavelength selective switch*
- 2007 *MicroDisk resonator infrared detector*
- 2005 *Si<sub>3</sub>N<sub>4</sub> low-loss waveguides*
- 2000 *SiON / SiO<sub>2</sub> (Clarendon Photonics)*
- 1990s *Si PhC & Optical MEMS*



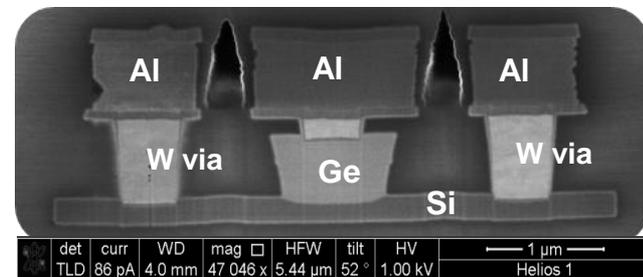
**24 GHz 0.7V-cm Travelling Wave MZI Modulator**



**Resonant Optical Modulator/Filter**

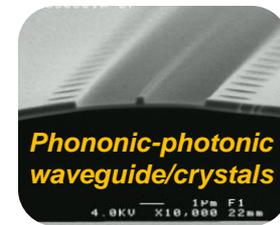
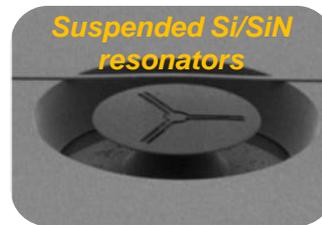
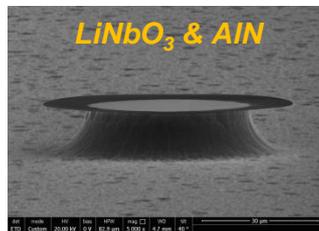


**Tunable Resonant Filter**



**45 GHz High-speed Ge Detector on Si**

**MEMS process for additional capability**

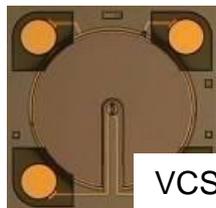


# Trusted Advanced Pathfinder Products: III-V Photonics

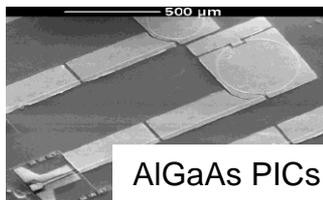
2010s



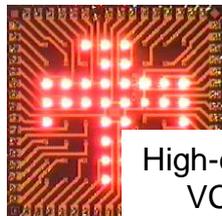
InGaAsP PICs



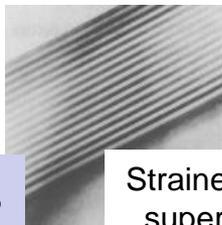
VCSEL+ PD



AlGaAs PICs

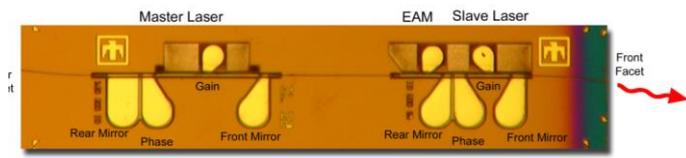


High-efficiency VCSELs

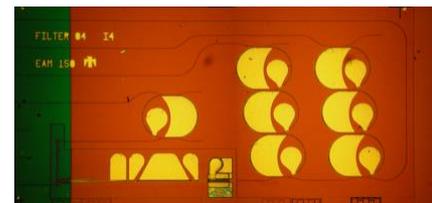


Strained-layer superlattices

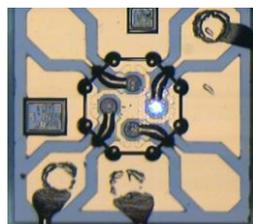
1980s



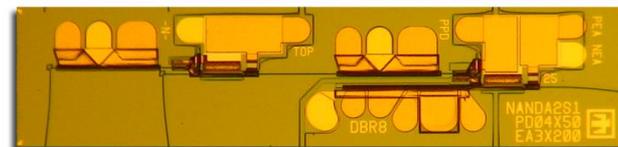
On-Chip Injection Locking  
Enhanced Modulation > 50 GHz, C-Band



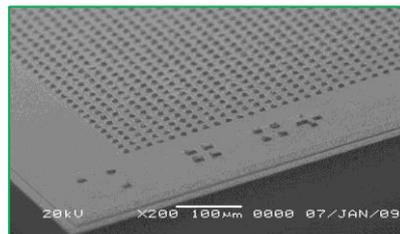
RF-Optical Channelizing Filter  
1-20 GHz RF on C-Band Light



Single-Frequency Tunable VCSELs,  
For atomic spectroscopy and sensors



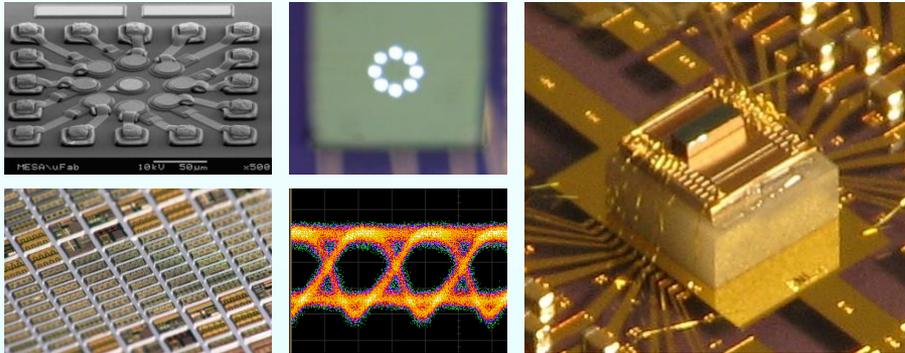
All-Optical Logic at >40 Gb/s, C-Band



nBn FPAs in the SWIR, MWIR and LWIR,  
leveraging novel III-P and III-Sb materials

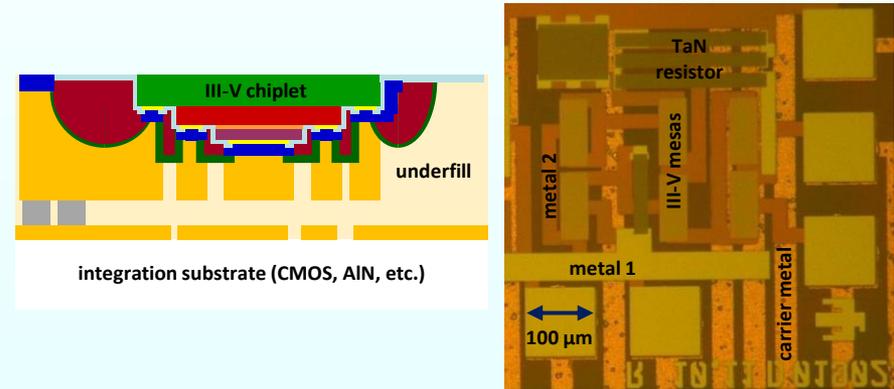
- **Foundational Capabilities**
  - III-V compound semiconductor epitaxy, microfabrication, integration
  - Device physics, modeling, simulation
  - Microelectronics/optoelectronics, and complex mono/hetero-circuits
- **Prove, Advance Technology Readiness Level, Productize**
  - TRL1-6+: create, develop, prototype
  - NNSA QMS/QC-1-10; trusted
- **Trusted, low-volume, high-reliability products for harsh environments**

## Optical Data Communications



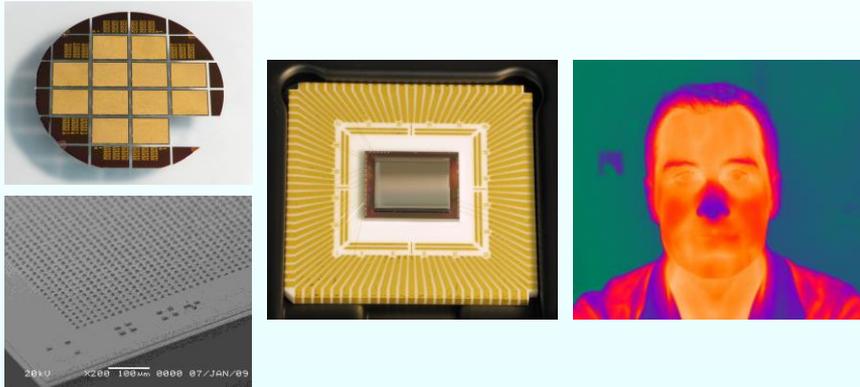
- GaAs- and InP-based devices: VCSELs, modulators, photodiodes
- dense integration onto 32-nm and 45-nm CMOS

## Heterogeneous III-V/CMOS Microelectronics



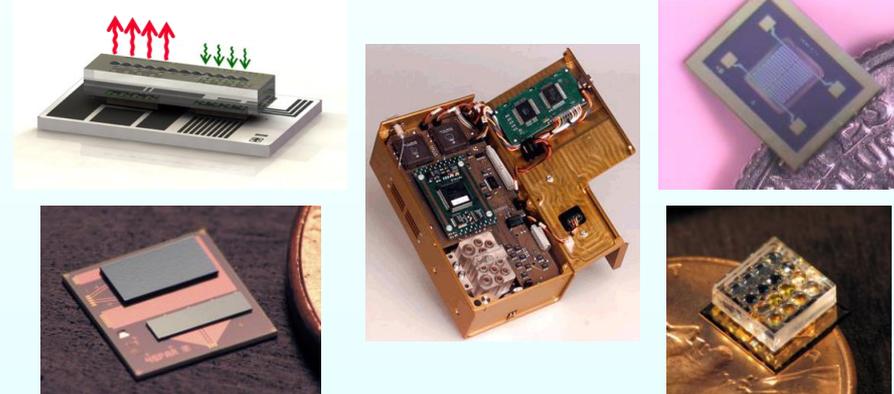
- complementary integration of GaAs and InP microelectronics
- III-V microelectronics circuitry on CMOS ASICs

## IR Imagers for Remote Sensing



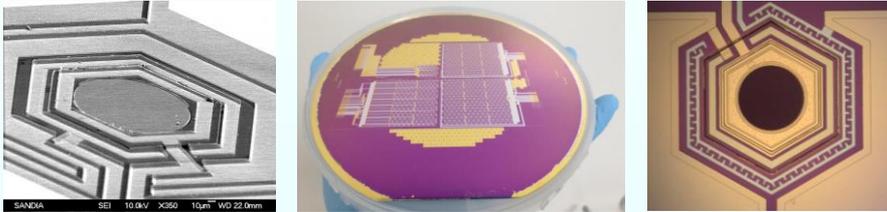
- nBn InAs/GaSb MWIR/LWIR detector arrays for large-format FPAs
- 10μm indium bump bonding, underfill, thinning, AR coating
- hybridization to silicon ROICs with >99.99% interconnect yield

## Optical and MEMS-based Microsensors



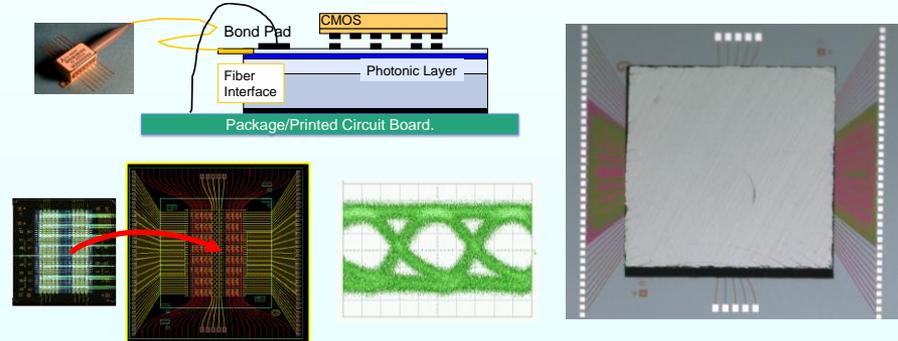
- chemical and bio sensors using MEMS and SAW devices
- g-hard optical microsensors with in-house photonics
- hybrid device integration with custom micro-optics

## Microsystem-Enabled Photovoltaics



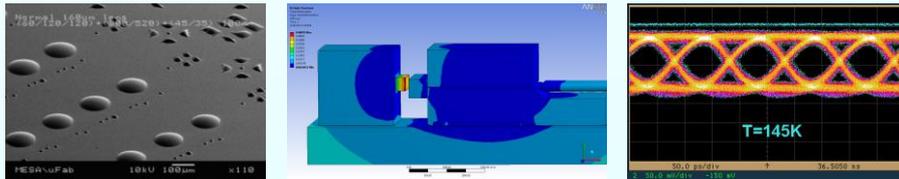
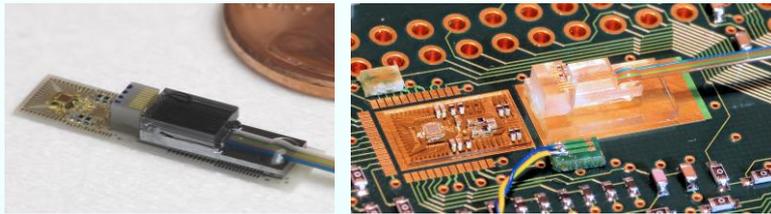
- wafer-level bonding for multi-junction solar cells
- InGaAsP/InP and InGaP/GaAs devices on silicon
- dielectric interfaces with III-V substrate removal
- integration with collection optics

## High Performance Computing



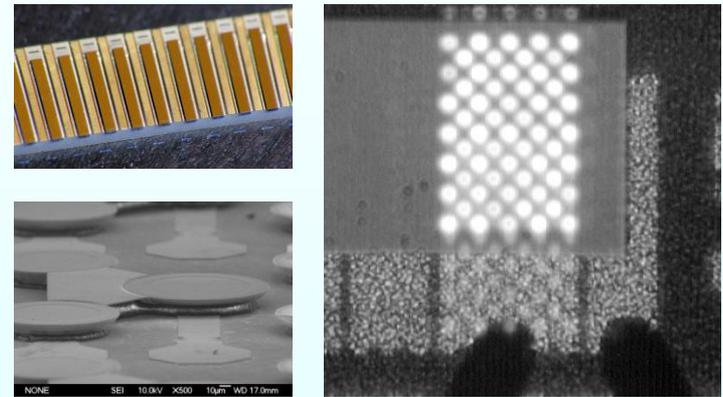
- silicon photonics on high-speed silicon ASIC
- independent optimization of electronics & photonics

## Extreme Environment Applications



- custom photonics, optics, electronics for cryogenic interconnects
- advanced optoelectronics and integration for radiation hardness

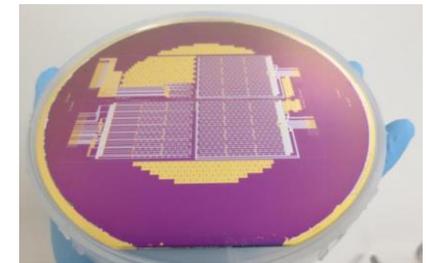
## High Performance Photonics



- high-power emitters on AlN and diamond
- RF packaging for high-speed test and measurement

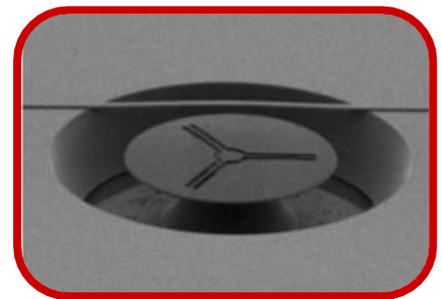
# Potential Roles and Engagement within The IP-IMI

- **Trusted Tech Transition:** ITAR, sensitive projects
- **Novel Materials, Devices, or process integration:**
  - Items outside primary scope of Institute?
- **Extra Fab/MPW and Test capacity**
  - Unique failure analysis and reliability tools also available



## Engagement

- DOE supporting National Lab involvement in strategy and project development for *ALL* teams.
- We are available for:
  - Telecons & briefings at team meetings
  - Hosting visits to Sandia



***Very strong teams have formed: What gaps can we help fill?***